To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

PRELIMINARY
Notice: This is not a final specification.
Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

FY6BGH-02F

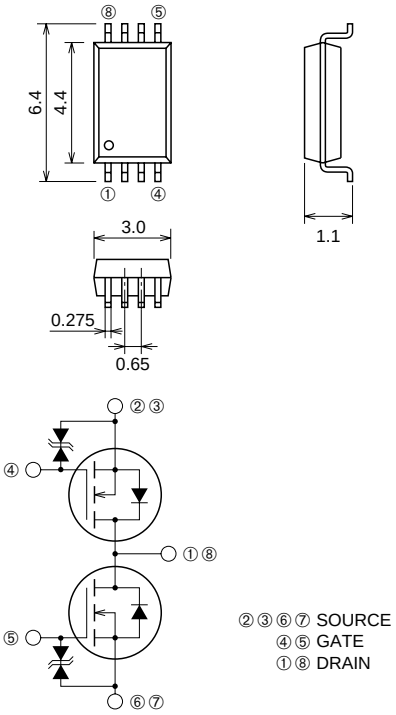
HIGH-SPEED SWITCHING USE

FY6BGH-02F



- DRAIN COMMON
- 2.5V DRIVE
- V_{DSS} 20V
- $r_{DS\ (ON)\ (MAX)}$ 25mΩ
- I_D 6A

OUTLINE DRAWING Dimensions in mm



TSSOP8

APPLICATION

Li - ion battery protection

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	V_{GS} = 0V	20	V
V_{GSS}	Gate-source voltage	V_{DS} = 0V	±10	V
I_D	Drain current		6	A
I_{DM}	Drain current (Pulsed)		42	A
I_{DA}	Avalanche current (Pulsed)	L = 10µH	6	A
I_S	Source current		1.3	A
I_{SM}	Source current (Pulsed)		5.2	A
P_D	Maximum power dissipation		1.4	W
T_{ch}	Channel temperature		–55 ~ +150	°C
T_{stg}	Storage temperature		–55 ~ +150	°C
—	Weight	Typical value	0.035	g

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PRELIMINARY
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ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)\ DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS} = 0V	20	—	—	V
$V_{(BR)\ GSS}$	Gate-source breakdown voltage	I_G = ±100μA, V_{DS} = 0V	±10	—	—	V
I_{GSS}	Gate-source leakage current	V_{GS} = ±10V, V_{DS} = 0V	—	—	±10	μA
I_{DSS}	Drain-source leakage current	V_{DS} = 20V, V_{GS} = 0V	—	—	0.1	mA
$V_{GS\ (th)}$	Gate-source threshold voltage	I_D = 1mA, V_{DS} = 10V	0.5	0.9	1.5	V
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 6A, V_{GS} = 4V	—	20	25	mΩ
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 3A, V_{GS} = 2.5V	—	25	35	mΩ
$V_{DS\ (ON)}$	Drain-source on-state voltage	I_D = 6A, V_{GS} = 4V	—	0.120	0.150	V
$\lvert y_{fs} \rvert$	Forward transfer admittance	I_D = 6A, V_{DS} = 10V	—	15	—	S
C_{iss}	Input capacitance	V_{DS} = 10V, V_{GS} = 0V, f = 1MHz	—	1150	—	pF
C_{oss}	Output capacitance		—	—	—	pF
C_{rss}	Reverse transfer capacitance		—	—	—	pF
$t_{d\ (on)}$	Turn-on delay time	V_{DD} = 10V, I_D = 3A, V_{GS} = 4V, R_{GEN} = R_{GS} = 50Ω	—	—	—	ns
t_r	Rise time		—	—	—	ns
$t_{d\ (off)}$	Turn-off delay time		—	—	—	ns
t_f	Fall time		—	—	—	ns
V_{SD}	Source-drain voltage	I_S = 1.3A, V_{GS} = 0V	—	0.85	1.1	V
$R_{th\ (ch-a)}$	Thermal resistance	Channel to ambient	—	—	89.3	°C/W
t_{rr}	Reverse recovery time	I_S = 1.3A, dis/dt = –50A/μs	—	50	—	ns

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